

TRIAC series

1 Description

16A series triacs with low holding and latchingcurrent are especially recommended for use onmiddle and small resistance type power load.

(TO-220Alns) series provide insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).

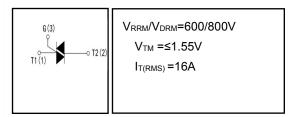
(TO-220F Ins) provides a rated insulation voltage of 2000VRMS, complying with UL standards (File ref: E252906).

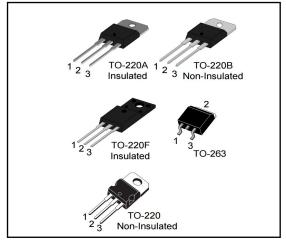
2 Features

- High current output up to 16A
- Low Peak on-state voltage drop
- High voltage
- High reliability

3 Applications

- jet pumps of dishwashers
- fans of air-conditioner
- power charger
- AC Motor control





4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25 °C, unless otherwise noted)

PARAMETER			SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (Tj=25°C)			V_{DRM}	600/800	V
Repetitive peak reverse voltage (Tj=25	℃)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state volt	age		V_{DSM}	+ 100	V
Non repetitive peak reverse voltage			V_{RSM}	+ 100	V
	TO-220(Ins)/TO-2	20F/(TC=85°C)			
RMS on-state current	TO-220/TO-263(N	lon)/(TC=110°C)	I _{T(RMS)}	16	A
	tp=8.3ms			170	А
Non repetitive surge peak on-state current tp=10ms		I _{TSM}	160		
I ² t value for fusing (tp=10ms)			l ² t	128	Α
Repetitive rate of rise of on-state current			d _{IT/dt}	50	A/us
(ITM=20A IG=50mA dIG/dt 50mA/ms)					
Peak gate current			I _{GM}	4	Α
Peak gate power			P _{GM}	10	W
Average gate power dissipation			P _{G(AV)}	1	W
Operating junction temperature range			TJ	- 40 ~ 125	$^{\circ}\mathbb{C}$
Storage junction temperature range			T _{STG}	- 40 ~ 150	$^{\circ}$ C

4.2 Thermal Characteristics

PARAMETER	SYMBOL		UNIT		
FARAWETER	STIVIBUL	TO-220(Non)	TO-220(Ins)	TO-220F/263	UNIT
Thermal Resistance, Junction to Case-sink	R _{thJC}	1.2	2.1	2.4	°C/W



4.3 Electrical Characteristics (Tc=25°C,unless otherwise noted)

SYMBOL	PARAMETER	Test Conditions		Min	Тур	Max	Unit
			I - II -III	-	-	35	
I _{GT}	Triggering gate current	$V_D=12V R_L=33\Omega$ IV		-	-	-	mA
V _{GT}	Triggering gate voltage		ALL	-	-	1.3	V
V_{GD}	Non-triggering gate voltage	$V_D = V_{DRM} T_j = 125 ^{\circ}CR_L = 3.3 K\Omega$		0.2	-	-	V
			I -III	-	-	50	
IL.	Latching Current	I _G =1.2I _{GT}	II	-	-	60	mA
lμ	Holding Current	I _T =500mA		-	-	50	mA
d _{V/dt}	Critical Rate of Rise of Off-state Voltage	V _D =2/3V _{DRM} Gate Open T _j =125°C		500	-	-	V/us
V _{TM}	Peak Forward On-State Voltage	I _{TM} =23A tp=380us		-	-	1.55	V
I _{DRM}	Maximum forward or reverse leakage current		Tj=25℃	-	-	5	uA
I _{RRM}	Maximum reverse leakage current	$V_D = V_{DRM} V_R = V_{RRM}$	Tj=125℃	-	-	2	mA

5 Typical characteristics diagrams

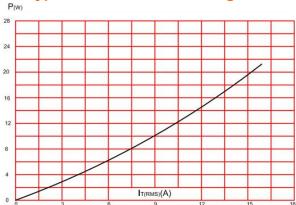


FIG.1: Maximum power dissipation versus RMS on-state current

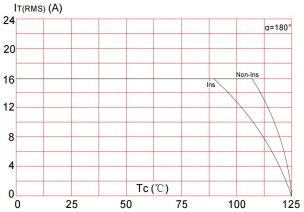


FIG.2: RMS on-state current versus case temperature

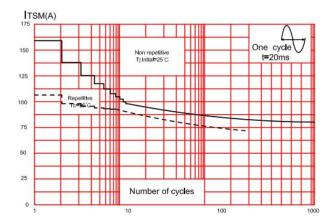


FIG.3: Surge peak on-state current versus number of cycles

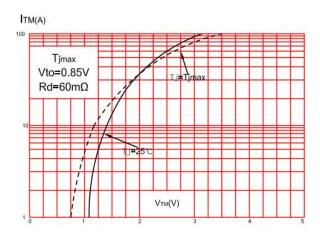


FIG.4: On-state characteristics (maximum values)



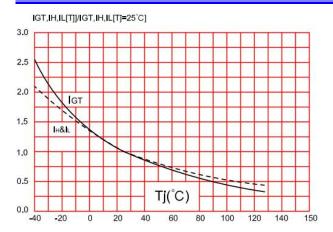
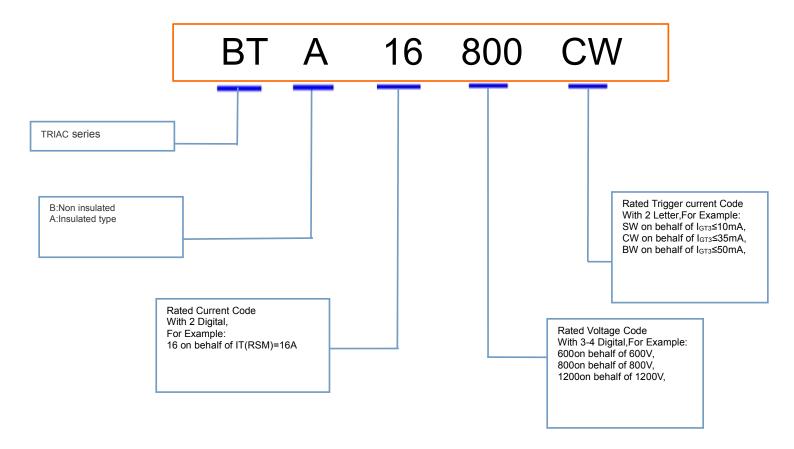


FIG.5: Relative variations of gate trigger current, holding current and latching current versus junction temperature

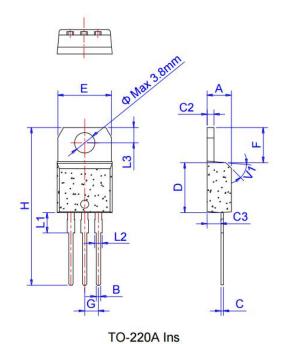
6 Product Names Rules



Inches



7 Dimensions

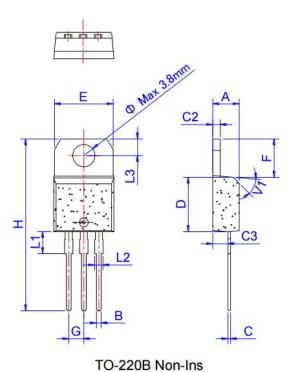


	Min.	Typ.	Max.	Min.	Тур.	Max.
Α	4.40		4.60	0.173		0.181
В	0.61		0.88	0.024		0.035
С	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
Е	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
Н	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	6

Dimensions

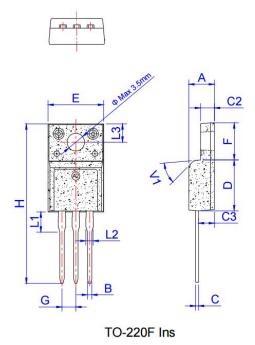
Millimeters

Ref.



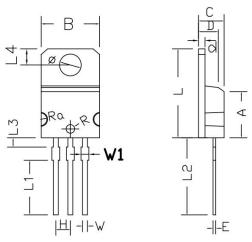
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C2	1.21		1.32	0.048		0.052		
C3	2.40		2.72	0.094		0.107		
D	8.60		9.70	0.339		0.382		
E	9.60		10.4	0.378		0.409		
F	6.20		6.60	0.244		0.260		
G		2.54			0.1			
Н	28.0		29.8	1.102		1.173		
L1		3.75			0.148			
L2	1.14		1.70	0.045		0.067		
L3	2.65		2.95	0.104		0.116		
V1		45°			45°			





	Dimensions							
Ref.		Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	4.50		4.90	0.177		0.193		
В	0.74	0.80	0.83	0.029	0.031	0.033		
С	0.47		0.65	0.019		0.026		
C2	2.45		2.75	0.096		0.108		
C3	2.60		3.00	0.102		0.118		
D	8.80		9.30	0.346		0.366		
E	9.80		10.4	0.386		0.410		
F	6.40		6.80	0.252		0.268		
G		2.54			0.1			
Н	28.0		29.8	1.102		1.173		
L1		3.63			0.143			
L2	1.14		1.70	0.045		0.067		
L3		3.30			0.130			
V1		45°			45°			

TO-220M PACKAGE OUTLINE DIMENSIONS



Cl 1	Dimensions 1	In Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	7. 55	8.05	0. 297	0. 317
В	9. 85	10. 25	0. 388	0. 404
C	4. 20	4.80	0. 165	0. 189
D	3. 20	3.60	0. 126	0. 142
Е	0.42	0. 47	0.017	0.019
L	15. 20	15. 60	0. 598	0.614
Н	2. 52	2. 56	0.099	0. 101
W	0.78	0.88	0.031	0.035
Φ	3.60	3.90	0. 142	0. 154
R	0.72	0.78	0.028	0.031
Ra	9.00	10. 5	0. 354	0.413
d	1. 10	1.40	0.043	0. 055
L1	9.3	9.7	0. 366	0. 382
L2	13.00	13.60	0. 512	0. 535
L3	1. 20	1.70	0.047	0.067
L4	2.60	3.0	0. 102	0.118
W1	1. 10	1.50	0.043	0.059



8 Attentions

- Jiangsu Donghai Semiconductor Technology Co., Ltd. reserves the right to change the specification
 without prior notice! The customer should obtain the latest version of the information before making
 the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of WXDH products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2017.09.22	1.0	Original	